

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant :	Shunpei Yamazaki, et al.	Art Unit :	Unknown
Serial No. :	New Application	Examiner :	Unknown
Filed :	December 5, 2003	Confirmation No.:	Unknown
Title :	THIN FILM TRANSISTORS AND SEMICONDUCTOR DEVICE		

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Under 35 USC §120, this application relies on the earlier filing date of application serial number 09/874,204, filed on June 6, 2001. The attached list of references were submitted to and/or cited by the Office in the prior application and, therefore, are not provided in this application.

This statement is being filed with the application. Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: December 5, 2003


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Substitute Form PTO-1449 (Modified)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12732-051002	Application No. New Application
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR §1.98(b))		Applicant Shunpei Yamazaki, et al.	
		Filing Date December 5, 2003	Group Art Unit Unknown

U.S. Patent Documents							
Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
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	AB	5,643,826	07/01/1997	Ohtani, et al.			
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Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

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	BA	6,495,886	12/17/2002	Yamazaki, et al.			06/13/2002
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							Yes	No
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	BR	

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